



For immediate release

Diodes Incorporated Introduces Dual Device MOSFETs in Ultra Small Packages

Space Saving Devices Increase Charger Performance for Portable Devices

Dallas, Texas – April 16, 2009 --- Diodes Incorporated (Nasdaq: DIOD), a leading global manufacturer and supplier of high-quality application specific standard products within the broad discrete and analog semiconductor markets, today announced the release of dual device MOSFET combinations in thermally efficient ultra small DFN packages for charging and switching applications in portable devices.

The DMS2220LFDB and DMS2120LFW co-package a 20V P-channel enhancement mode MOSFET with a companion diode in either a 2mm x 2mm DFN2020 or 3mm x 2mm DFN3020 package. The DMP2160UFDB co-packages two of the same MOSFETs in the DFN2020 format.

Compared to larger 3mm x 3mm footprint packages traditionally used in portable application designs, the DFN2020 utilizes 55 percent less PCB space. Additionally, with an off-board height of only 0.5mm, the package is also 50 percent thinner, suiting next-generation product design. The MOSFETs used in these packages feature low gate charge (Qg) and a typical $R_{DS(ON)}$ of 86m Ω at V_{GS} of 1.8V, ensuring that both switching and on state losses are minimized.

To further improve efficiency, the diode employed in these packages is the Company's own high performance SBR[®] rectifier. With a typical low forward voltage of only 0.42V, the SBR[®] offers a significant reduction in power dissipation compared to conventional Schottky diodes.

About Diodes Incorporated

Diodes Incorporated (Nasdaq: DIOD), an S&P SmallCap 600 and Russell 3000 Index company, is a leading global manufacturer and supplier of high-quality application specific standard products within the broad discrete and analog semiconductor markets, serving the consumer electronics, computing, communications, industrial and automotive markets. Diodes' products include diodes, rectifiers, transistors, MOSFETs, protection devices, functional specific arrays, amplifiers and comparators, Hall-effect sensors and temperature sensors, power management devices including LED drivers, DC-DC switching regulators, linear voltage regulators and voltage references along with special function devices including USB power switch, load switch, voltage supervisor and motor controllers. The Company's corporate headquarters are located in Dallas, Texas. A sales, marketing, engineering and logistics office is located in Westlake Village, California. Design centers are located in Dallas; San Jose, California; Taipei, Taiwan; Manchester, England and Neuhaus, Germany. The Company's wafer fabrication facilities are located in Kansas City, Missouri and Manchester; with two manufacturing facilities located in Shanghai, China, another in Neuhaus, and a joint venture facility located in Chengdu, China. Additional engineering, sales, warehouse and logistics offices are located in Taipei; Hong Kong; Manchester and Munich, Germany, with support offices located throughout the world. For further information, including SEC filings, visit the Company's website at <http://www.diodes.com>.

SBR is a registered trademark of Diodes Incorporated

#

Ian Moulding
MOSFET Products Marketing Manager
Diodes Incorporated
P: +44 161 622 4444
E: ian_moulding@eu.diodes.com

Shelton Group
Leanne K. Sievers
Investor Relations
P: 949-224-3874
E: lsievers@sheltongroup.com